

Docket No.: 61352-051



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| In re Application of | : | Customer Number: 20277 |
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| Yoshiaki HASEGAWA, et al. | : | Confirmation Number: 4412 |
| | : | |
| Serial No.: 10/687,647 | : | Group Art Unit: 2811 |
| | : | |
| Filed: October 20, 2003 | : | Examiner: Unknown |
| | : | |
| For: METHOD FOR FABRICATING SEMICONDUCTOR LIGHT EMITTING DEVICE | | |

INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents and Trademarks
Washington, D. C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed with the application and no certification or fee is required.

The relevance of the references listed on attached Form 1449 is discussed in the present specification.

Japanese Unexamined Publication P2001-244560A was cited by the Inventors.

A copy of the foreign search report is attached for the Examiner's information.

Please note this is a PCT application in the entry of the National Phase in the U.S. and

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copies of the references cited were transmitted by WIPO and are believed to be in the file of the above identified application and readily available to the Examiner. However, to ensure that these references are available to the Examiner, we are providing copies of these references herewith. Since the Search Report was from the U.S. JPO or EPO search authorities, copies of these references should have been supplied to the USPTO under the trilateral agreement and are believed to be in the file of the above identified application and readily available to the Examiner. Therefore it is believed that Applicants have met all requirements regarding duty of disclosure under 37 CFR 1.56. Acknowledgement and consideration of these documents are respectfully requested.

Respectfully submitted,

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| INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449) | | | | ATTY. DOCKET NO. 61352-051 | | SERIAL NO. 10/687,647 | |
| | | | | APPLICANT Yoshiaki HASEGAWA, et al. | | | |
| | | | | FILING DATE October 20, 2003 | | GROUP 2811 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Code2 (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | | |
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| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | | | | |
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| EXAMINER | | | | DATE CONSIDERED | | | |

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.